

ATOMICALLY FLAT 6H-SiC

In-situ-etched semi-insulating vanadium-compensated nominally on-axis 500- μ m-thick 6H-SiC(0001)

Available formats: 15 mm \times 15 mm or 20 mm \times 20 mm

Parameter at 300 K	Min	Max	Units
Resistivity	1E9	—	Ω cm

ATOMICALLY FLAT 4H-SiC

In-situ-etched semi-insulating high-purity nominally on-axis 500- μ m-thick 4H-SiC(0001)

Available formats: 15 mm \times 15 mm or 20 mm \times 20 mm

Parameter at 300 K	Min	Max	Units
Resistivity	1E7	—	cm^{-2}

GRAPHENE ON 6H-SiC

Transfer-free p-type hydrogen-intercalated quasi-free-standing epitaxial Chemical Vapor Deposition graphene on semi-insulating vanadium-compensated nominally on-axis 500- μ m-thick 6H-SiC(0001)

Available formats: 15 mm \times 15 mm or 20 mm \times 20 mm

Parameter at 300 K	Min	Max	Units
Hole concentration	7.5E12	8.5E12	cm^{-2}
Hole mobility	3000	5000	cm^2/Vs
Sheet resistance	100	300	Ω/sq

GRAPHENE ON 4H-SiC

Transfer-free p-type hydrogen-intercalated quasi-free-standing epitaxial Chemical Vapor Deposition graphene on semi-insulating high-purity nominally on-axis 500- μ m-thick 4H-SiC(0001)

Available formats: 15 mm \times 15 mm or 20 mm \times 20 mm

Parameter at 300 K	Min	Max	Units
Hole concentration	1.2 E13	1.3 E13	cm^{-2}
Hole mobility	3000	5000	cm^2/Vs
Sheet resistance	100	300	Ω/sq

AMORPHOUS Al_2O_3

Amorphous atomic-layer-deposited aluminum oxide on custom substrate

Available formats: up to 4 inch

Available thickness: 10 nm to 100 nm

Parameter at 300 K	Min	Max	Units
Density	2.0	3.0	g/cm^3
Refractive index	1.6	1.8	NA